

IXFP130N10T

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IXFP130N10T Information

	Part Number Manufacturer Category		
www.heiseper.com	Description Package	Transistors - FETs, MOSFETs - Single MOSFET N-CH 100V 130A TO-220 TO-220-3	
For Reference Only	T uchuge	For the pricing/inventory/lead time, please contact us Website: https://www.heisener.com	
For Reference Only		Website: https://www.heisener.com E-mail: salesdept@heisener.com	

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IXFP130N10T Specifications

Manufacturer Part Number IXFP130N10T Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Transistors - FETs, MOSFETs - Single Package T0-220-3 Series TrenchMV? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 104AC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) - FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
CategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageT0-220-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)00VCurrent - Continuous Drain (Id) @ 25°C30A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ ImAGate Charge (Qg) (Max) @ Vgs080pF @ 25VYog (Max).FET Feature-Power Dissipation (Max)9.1 mOhm @ 25A, 10VRds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOprating Type.55° C ~ 175°C (TJ)Mounting TypeTo-220ABPackage / CaseT0-220AB	Manufacturer Part Number	IXFP130N10T
Transistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C130A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 1mAGate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Manufacturer	IXYS
PackageTO-220-3SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C130A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ ImAGate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Category	Discrete Semiconductor Products
SeriesTrenchMV?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C30A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ ImAGate Charge (Qg) (Max) @ Vgs104C @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)60W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C130A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 1mAGate Charge (Qg) (Max) @ Vgs104n C @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C130A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 1mAGate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	TrenchMV?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C130A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 1mAGate Charge (Qg) (Max) @ Vgs104n C @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 130A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 104nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) - FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 1mAGate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Fer Feature360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	100V
Ygs(th) (Max) @ Id 4.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 104nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5080pF @ 25V Vgs (Max) - Ygs (Max) - FET Feature - Power Dissipation (Max) 360W (Tc) Rds On (Max) @ Id, Vgs 9.1 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB	Current - Continuous Drain (Id) @ 25°C	130A (Tc)
Gate Charge (Qg) (Max) @ Vgs104nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds5080pF @ 25VVgs (Max)-FGT Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Vgs(th) (Max) @ Id	4.5V @ 1mA
Vgs (Max)-FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	104nC @ 10V
FET Feature-Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Input Capacitance (Ciss) (Max) @ Vds	5080pF @ 25V
Power Dissipation (Max)360W (Tc)Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Vgs (Max)	-
Rds On (Max) @ Id, Vgs9.1 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Power Dissipation (Max)	360W (Tc)
Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Rds On (Max) @ Id, Vgs	9.1 mOhm @ 25A, 10V
Supplier Device PackageTO-220ABPackage / CaseTO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IXFP130N10T Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFP130N10T Payment Methods



IXFP130N10T Shipping Methods



If you have any question about IXFP130N10T, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com